Arijit Roy

List of Publications by Year
in descending order

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		1040056	794594
23	453	9	19
papers	citations	h-index	g-index

23	23	23	287
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	An efficient method of detection of COVID-19 using Mask R-CNN on chest X-Ray images. AIMS Biophysics, 2021, 8, 281-290.	0.6	16
2	An experimental method of bioimpedance measurement and analysis for discriminating tissues of fruit or vegetable. AIMS Biophysics, 2020, 7, 41-53.	0.6	5
3	Measurement of bioimpedance and application of Cole model to study the effect of moisturizing cream on human skin. AIMS Biophysics, 2020, 7, 362-379.	0.6	4
4	Inadequacy of Markov Model in Modeling of Electromigration-Induced Resistance Degradation. , 2018, , .		1
5	Experimenting and modeling of catastrophic failure in electromigration-induced resistance degradation for deep submicron dual-damascene copper interconnects. Solid-State Electronics, 2018, 148, 7-15.	1.4	4
6	Multiple data access via a common cavity bus in circuit QED. International Journal of Circuit Theory and Applications, 2017, 45, 970-988.	2.0	1
7	Proposal of a transmon-based high bandwidth quantum router. , 2017, , .		0
8	Design of efficient loadcell for measurement of mechanical impact by piezoelectric PVDF film sensor. AIP Advances, 2016, 6, 095122.	1.3	9
9	Microstructure Measurement Techniques for Studying Electromigration in ULSI Interconnects. Critical Reviews in Solid State and Materials Sciences, 2016, 41, 159-191.	12.3	3
10	A transmon-based quantum half-adder scheme. Progress of Theoretical and Experimental Physics, 2015, 2015, 093A02.	6.6	8
11	Fabrication and characterization of copper interconnects of line-width down to 100nm using a specially designed phase shift mask. Microelectronic Engineering, 2014, 113, 152-156.	2.4	5
12	Dynamics of electromigration induced void in submicron Cu interconnects. , 2011, , .		3
13	Electromigration in width transition copper interconnect. Microelectronics Reliability, 2009, 49, 1086-1089.	1.7	3
14	Very high current density package level electromigration test for copper interconnects. Journal of Applied Physics, 2008, 103, 093707.	2.5	22
15	Application of gamma distribution in electromigration for submicron interconnects. Journal of Applied Physics, 2007, 102, .	2.5	20
16	Room temperature observation of point defect on gold surface using thermovoltage mapping. Microelectronics Reliability, 2007, 47, 1580-1584.	1.7	0
17	Probing into the asymmetric nature of electromigration performance of submicron interconnect via structure. Thin Solid Films, 2007, 515, 3867-3874.	1.8	28
18	Electromigration in ULSI interconnects. Materials Science and Engineering Reports, 2007, 58, 1-75.	31.8	198

#	Article	IF	Citations
19	Experimental investigation on the impact of stress free temperature on the electromigration performance of copper dual damascene submicron interconnect. Microelectronics Reliability, 2006, 46, 1652-1656.	1.7	23
20	Investigation of the effect of temperature and stress gradients on accelerated EM test for Cu narrow interconnects. Thin Solid Films, 2006, 504, 288-293.	1.8	62
21	Electromigration in damascene copper interconnects of line width down to 100 nm. Semiconductor Science and Technology, 2006, 21, 1369-1372.	2.0	15
22	Effect of test condition and stress free temperature on the electromigration failure of Cu dual damascene submicron interconnect line-via test structures. Microelectronics Reliability, 2005, 45, 1443-1448.	1.7	18
23	Effect of vacuum break after the barrier layer deposition on the electromigration performance of aluminum based line interconnects. Microelectronics Reliability, 2005, 45, 1449-1454.	1.7	5